AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A perpendicular magnetic recording disk for use in perpendicular magnetic recording, said perpendicular magnetic recording disk characterized by comprising a substrate, a soft magnetic layer of a material selected from a group consisting of an Fe-based material and a Co-based material on said substrate, a ferromagnetic layer on said soft magnetic layer, having a granular structure, and comprising crystal gains mainly made of cobalt (Co) and grain boundary portions mainly made of ~~a material selected from a group consisting of an oxide, silicon (Si), and an oxide of silicon (Si)~~ SiO_2, and a layer, on said ferromagnetic layer, comprising a material selected from a group consisting of CoCrPt, CoPt, CoPd, FePt, $CoPt_3$, and $CoPd_3$, the content of the ~~silicon (Si)~~ SiO_2 in said ferromagnetic layer being 6at% or more.

2. - 4. (canceled).

5. (currently amended): A perpendicular magnetic recording disk according to claim 1, characterized in that a spacer layer selected from a group consisting of a Pd layer and a Pt layer is provided between said ferromagnetic layer and said layer comprising ~~a~~ the material selected from ~~a~~ the group consisting of CoCrPt, CoPt, CoPd, FePt, $CoPt_3$, and $CoPd_3$.

6. (currently amended): A method of manufacturing a perpendicular magnetic recording disk for use in perpendicular magnetic recording and having at least a soft magnetic layer of a material selected from a group consisting of an Fe-based material and a Co-based material on a substrate and a magnetic recording layer on said soft magnetic layer, said method characterized by,

in a step of forming said magnetic recording layer comprising, on said soft magnetic layer, a ferromagnetic layer of a granular structure comprising ~~silicon (Si) or an oxide of silicon (Si)~~ SiO_2, between crystal grains comprising cobalt (Co), the content of the ~~silicon (Si)~~ SiO_2 in said ferromagnetic layer being 6at% or more, and a stacked layer, on said ferromagnetic layer, comprising a material selected from a group consisting of CoCrPt, CoPt, CoPd, FePt, $CoPt_3$, and $CoPd_3$, forming said ferromagnetic layer on said soft magnetic layer by sputtering in an argon gas atmosphere and then forming said stacked layer comprising the material selected from the group consisting of CoCrPt, CoPt, CoPd, FePt, $CoPt_3$, and $CoPd_3$ by sputtering in an argon gas atmosphere at a gas pressure lower than a gas pressure used when forming said ferromagnetic layer.

7. - 10. (canceled)